

NEC's NPN SiGe HIGH FREQUENCY TRANSISTOR

NESG3031M14

FEATURES

 THE DEVICE IS AN IDEAL CHOICE FOR LOW NOISE, HIGH-GAIN AMPLIFICATION:

NF = 0.95 dB TYP, G_a = 10.0 dB TYP. @ V_{CE} = 2 V, I_C = 6 mA, f = 5.2 GHz NF = 1.1 dB TYP, G_a = 9.5 dB TYP. @ V_{CE} = 2 V, I_C = 6 mA, f = 5.8 GHz

MAXIMUM STABLE POWER GAIN:

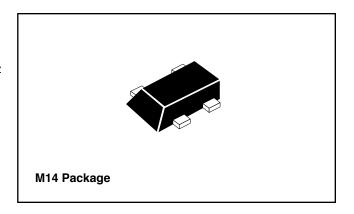
MSG = 15.0 dB TYP. @ VcE = 3 V, Ic = 20 mA, f = 5.8 GHz

· SiGe HBT TECHNOLOGY (UHS3) ADOPTED:

 $f_{max} = 110 GHz$

M14 PACKAGE:

4-pin lead-less minimold package



ORDERING INFORMATION

PART NUMBER	QUANTITY	SUPPLYING FORM		
NESG3031M14-A	50 pcs (Non reel)	8 mm wide embossed taping		
NESG3031M14-T3-A	10 kpcs/reel	Pin 1 (Collector), Pin 4 (Emitter) face the perforation side of the tape		

Remark To order evaluation samples, contact your nearby sales office. Unit sample quantity is 50 pcs.

ABSOLUTE MAXIMUM RATINGS (TA = +25°C)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector to Base Voltage	VcBo	12.0	V
Collector to Emitter Voltage	VCEO	4.3	V
Emitter to Base Voltage	V _{EBO}	1.5	٧
Collector Current	Ic	35	mA
Total Power Dissipation	P _{tot} Note	150	mW
Junction Temperature	Tj	150	°C
Storage Temperature	T _{stg}	-65 to +150	°C

Note Mounted on 1.08 cm² × 1.0 mm (t) glass epoxy PWB

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

California Eastern Laboratories

ELECTRICAL CHARACTERISTICS (TA = +25°C)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
DC Characteristics				•	•	
Collector Cut-off Current	Ісво	V _{CB} = 5 V, I _E = 0 mA	_	_	100	nA
Emitter Cut-off Current	ІЕВО	V _{EB} = 1 V, I _C = 0 mA	-	-	100	nA
DC Current Gain	hFE Note 1	Vce = 2 V, Ic = 6 mA	220	300	380	-
RF Characteristics	•					
Insertion Power Gain	I S _{21e} I ²	VcE = 3 V, Ic = 20 mA, f = 5.8 GHz	6.5	9.0	_	dB
Noise Figure (1)	NF	VcE = 2 V, Ic = 6 mA, f = 5.2 GHz,	_	0.95	_	dB
		$Z_S = Z_{Sopt}, Z_L = Z_{Lopt}$				
Noise Figure (2)	NF	$V_{CE} = 2 \text{ V}, \text{ Ic} = 6 \text{ mA}, \text{ f} = 5.8 \text{ GHz},$	-	1.1	1.5	dB
		$Z_S = Z_{Sopt}, Z_L = Z_{Lopt}$				
Associated Gain (1)	Ga	$V_{CE} = 2 \text{ V}, \text{ Ic} = 6 \text{ mA}, \text{ f} = 5.2 \text{ GHz},$	_	10.0	_	dB
		$Z_S = Z_{Sopt}, Z_L = Z_{Lopt}$				
Associated Gain (2)	Ga	$V_{CE} = 2 \text{ V}, \text{ Ic} = 6 \text{ mA}, \text{ f} = 5.8 \text{ GHz},$	7.5	9.5	_	dB
		$Z_S = Z_{Sopt}, Z_L = Z_{Lopt}$				
Reverse Transfer Capacitance	Cre Note 2	V _{CB} = 2 V, I _E = 0 mA, f = 1 MHz	-	0.15	0.25	pF
Maximum Stable Power Gain	MSGNote 3	VcE = 3 V, Ic = 20 mA, f = 5.8 GHz	12.0	15.0	_	dB
Gain 1 dB Compression Output Power	Po (1 dB)	Vce = 3 V, Ic (set) = 20 mA,	_	13.0	_	dBm
		f = 5.8 GHz, Zs = Zsopt, ZL = ZLopt				
3rd Order Intermodulation Distortion	OIP₃	VcE = 3 V, Ic (set) = 20 mA,	-	18.0	_	dBm
Output Intercept Point		f = 5.8 GHz, Zs = Zsopt, ZL = ZLopt				

Notes 1. Pulse measurement: PW \leq 350 μ s, Duty Cycle \leq 2%

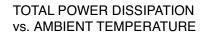
2. Collector to base capacitance when the emitter grounded

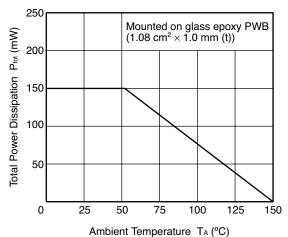
3. MSG =
$$\left| \frac{S_{21}}{S_{12}} \right|$$

hfe CLASSIFICATION

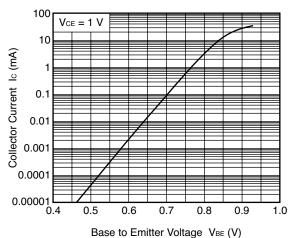
RANK	FB
Marking	zJ
hfe Value	220 to 380

TYPICAL CHARACTERISTICS (TA = 25°C, unless otherwise specified)

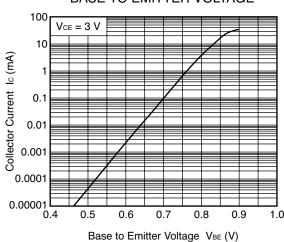




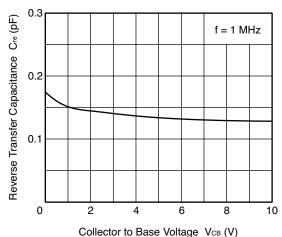
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



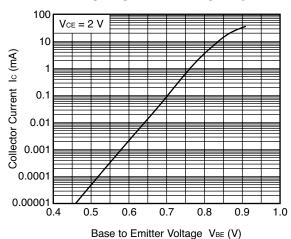
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



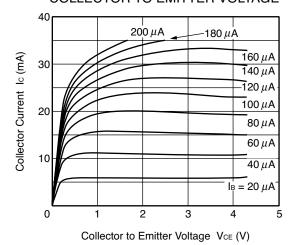
REVERSE TRANSFER CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE



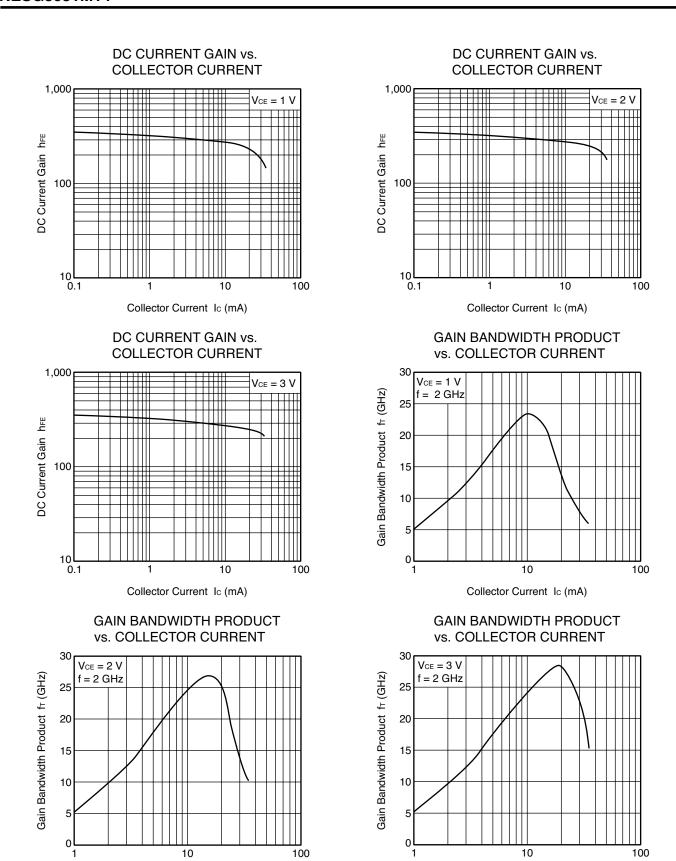
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



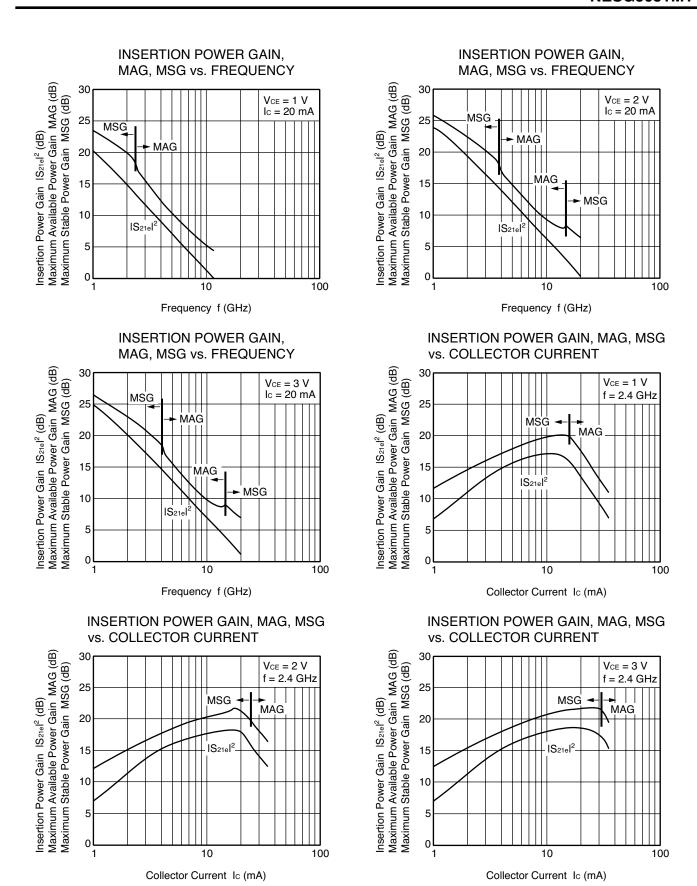
Remark The graphs indicate nominal characteristics.



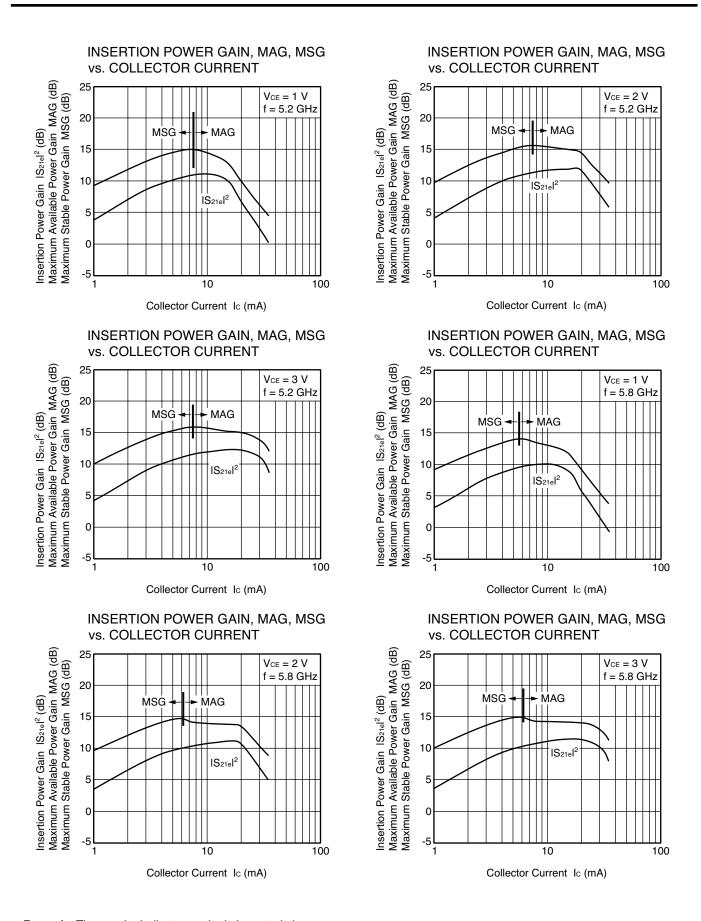
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Collector Current Ic (mA)

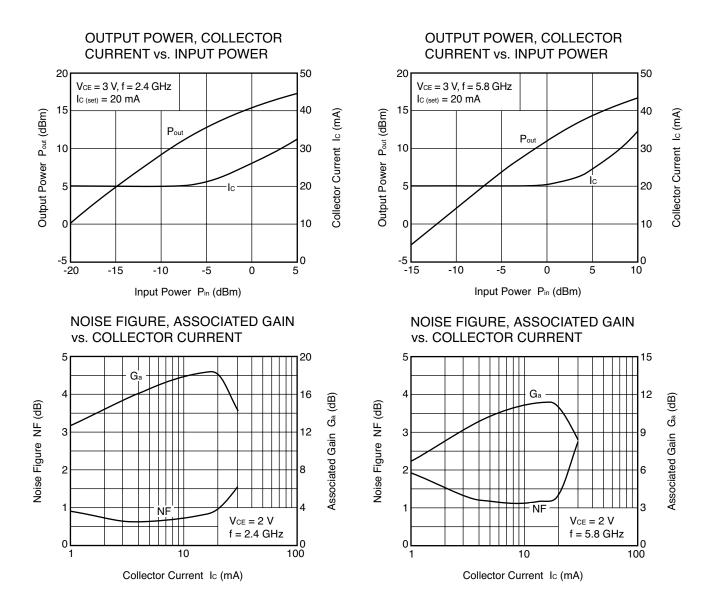
Collector Current Ic (mA)



Remark The graphs indicate nominal characteristics.



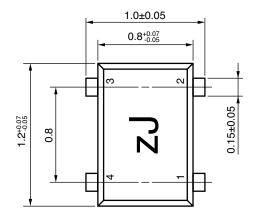
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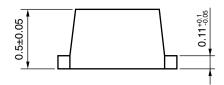


Remark The graphs indicate nominal characteristics.

PACKAGE DIMENSIONS (UNIT: mm)

4-PIN LEAD-LESS MINIMOLD (M14, 1208 PACKAGE)





PIN CONNECTIONS

- 1. Collector
- 2. Emitter
- 3. Base
- 4. Emitter

Life Support Applications

These NEC products are not intended for use in life support devices, appliances, or systems where the malfunction of these products can reasonably be expected to result in personal injury. The customers of CEL using or selling these products for use in such applications do so at their own risk and agree to fully indemnify CEL for all damages resulting from such improper use or sale.

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DATA SUBJECT TO CHANGE WITHOUT NOTICE

01/31/2005





Subject: Compliance with EU Directives

CEL certifies, to its knowledge, that semiconductor and laser products detailed below are compliant with the requirements of European Union (EU) Directive 2002/95/EC Restriction on Use of Hazardous Substances in electrical and electronic equipment (RoHS) and the requirements of EU Directive 2003/11/EC Restriction on Penta and Octa BDE.

CEL Pb-free products have the same base part number with a suffix added. The suffix –A indicates that the device is Pb-free. The –AZ suffix is used to designate devices containing Pb which are exempted from the requirement of RoHS directive (*). In all cases the devices have Pb-free terminals. All devices with these suffixes meet the requirements of the RoHS directive.

This status is based on CEL's understanding of the EU Directives and knowledge of the materials that go into its products as of the date of disclosure of this information.

Restricted Substance per RoHS	Concentration Limit per RoHS (values are not yet fixed)	Concentration contained in CEL devices		
Lead (Pb)	< 1000 PPM	-A Not Detected	-AZ (*)	
Mercury	< 1000 PPM	Not Detected		
Cadmium	< 100 PPM	Not Detected		
Hexavalent Chromium	< 1000 PPM	Not Detected		
PBB	< 1000 PPM	Not Detected		
PBDE	< 1000 PPM	Not Detected		

If you should have any additional questions regarding our devices and compliance to environmental standards, please do not hesitate to contact your local representative.

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In no event shall CEL's liability arising out of such information exceed the total purchase price of the CEL part(s) at issue sold by CEL to customer on an annual basis.

See CEL Terms and Conditions for additional clarification of warranties and liability.